

 Approved by government of Maharashtra

> Affiliated to Rashtrasant Tukadoji Maharaj Nagpur University, Nagpur

 Recognised by U.G.C New Delhi under section 2 (f) & 12 (b) of UGC act 1956

Bsc Physic Sem - IV

Paper 2 (Solid state electronics, and Molecular physics)

Question Bank

- 1. Considering transistor as two port device, write h-parameter equations for transistor in common emitter mode. Define h-parameters of a transistor in CE mode. Why these parameters are called hybrid parameter ?
- 2. Explain the construction and working of light emitting diode.
- 3. Calculate the energy band gap of Ga As P semiconducting material of LED with output light having wavelength 6715 Å. (Given : $q = 1.6 \times 10^{-19}$ C, $C = 3 \times 10^8$ m/s, $h = 6.626 \times 10^{-34}$ J-s)
- 4. Draw the circuit diagram of common emitter transistor amplifier and explain its working
- 5. A germanium transistor has a collector cut-off current ICBO = 14 μ A at room temperature and b = 50. It is used in common emitter amplifier.
- 6. Calculate the collector current when base current I B = 0.2 μ A. (ii) Assuming b does not change with temperature, find the new collector current, if the temperature of the transistor rises through 50°C.
- 7. Explain construction and working of solar cell.
- 8. What is stabilization? Explain the necessity of bias stabilization of transistor amplifier circuit.
- 9. What is MOSFET? What are different types of MOSFETs ? Discuss the drain and transfer characteristics of n-channel depletion MOSFETs.
- 10.Draw the circuit diagram of JFET as an amplifier. Explain its working.
- 11.Calculate the voltage gain of JFET voltage amplifier having transconductance 4000 μ mho and the load resistance 10 kW
- 12. What is JFET ? Explain the output characteristics of a JFET.
- 13.Define transconductance, drain resistance and amplification factor in JFET. State the relation between them.
- 14.Draw the well labelled diagram showing the construction of p-channel enhancement MOSFET. State special features of MOSFETs.
- 15. Give the theory of origin of pure rotational spectra for a di atomic molecule. Write the selection rules for it.
- 16.Discuss the different type of rigid molecules on the basis of their moment of inertia.



Mahila Vikas Sanstha's INDRAPRASTHA NEW ARTS COMMERCE & SCIENCE

COLLEGE, AT POST NALWADI, DIST. WARDHA (M.S.) Accredited 'B' by NAAC Approved by government of Maharashtra

> Affiliated to Rashtrasant Tukadoji Maharaj Nagpur University, Nagpur

> > Recognised by U.G.C New Delhi under section 2 (f) & 12 (b) of UGC act 1956

- 17.The spacing of a series of line in the microwave spectrum of AIH is constant at 12.604 cm–1. Calculate the moment of inertia of AIH molecule about its axis of rotation. (h = $6.602 \times 10-27$ erg-s).
- 18. Discuss in brief Born-Oppenheimer approximation
- 19.Draw the energy level diagram for the allowed transitions in rotation-vibration emission spectra when the vibrational transition takes place between V = 1 to V = 0.
- 20.Explain the intensity distribution of rotational spectral lines.
- 21.Moment of inertia of carbon monooxide molecule is $1.46\times10^{-46}~kg\text{-m}^2$. Calculate the energy of this molecule in lowest rotational energy level in eV.
- 22. What is Raman effect ? Explain Raman effect using quantum theory.
- 23.Describe the experimental arrangement to study the Raman effect.
- 24.For the exciting line of 4358 Å spectrum of benzene shows Raman lines for Dn = 608, 846, 995 and 1178 cm–1. If Benzene is irradiated by monochromatic light of wavelength 5461Å, what will be the wavelength of Raman lines for benzene.
- 25.State Frank-Condon principle. Explain morse curve.
- 26.Explain Electron Spin Resonance (ESR).
- 27.A substance shows a Raman line at 4567 Å when exciting line 4358 Å is used. Deduce the position of stokes' and anti-stokes' lines for the same substance when the exciting line 4047 Å is used.
- 28.Draw main components of Nuclear Magnetic Resonance Spectrometer. State any four applications of NMR.
- 29. State necessity of heat sink in transistor.
- 30.Draw the transfer characteristics of transistor in common emitter mode.
- 31. The current gain for a transistor is b = 350. Calculate the current gain a.
- 32. Why MOSFETs have higher input resistance than JFET ?
- 33.Define pinch off voltage in a JFET.
- 34.In a FET, transconductance is 6 mA/V, when reverse gate to source voltage changes by 0.2 V. Find corresponding change in drain current.
- 35. Why homonuclear molecule H2 and N2 donot show rotational spectra ?
- 36.The force constant for HCl molecule is 468.2 N/m and reduced mass of HCl molecule is 1.556×10^{-27} kg. What is the natural frequency of vibration of HClmolecule ?
- 37. Why a monochromatic source is necessary to study Raman effect?
- 38. With the exciting line 4358 Å a sample gives stokes' line at 4458 Å. Express this stokes' line in wave number.
- 39.Define h-parameters; obtain fundamental equation of a transistor in C.E mode and draw h-parameter equivalent circuit for it.



Mahila Vikas Sanstha's INDRAPRASTHA NEW ARTS COMMERCE & SCIENCE

COLLEGE, AT POST NALWADI, DIST. WARDHA (M.S.) Accredited 'B' by NAAC Approved by government of Maharashtra

> Affiliated to Rashtrasant Tukadoji Maharaj Nagpur University, Nagpur

 Recognised by U.G.C New Delhi under section 2 (f) & 12 (b) of UGC act 1956

- 40.Draw the circuit diagram of a common emitter NPN transistor amplifier and explain its working in brief.
- 41.For a transistor the collector current is 10.525 mA, leakage current ICBO is 5 mA when base current is 100 mA. Calculate the value of β .
- 42.Explain the working of NPN transistor.
- 43.Define stability factor. Why does the transistor require special biasing in CE mode ?
- 44.Draw the output characteristics of a transistor connected in common base mode and explain the three regions.
- 45.A transistor having hie = 800 W, hfe = 50, hoe = $80 \times 10-6$, and hre = 2.5×10^4 is used as a CE amplifier. If load resistance is 5 kW and effective source resistance is 500 W; calculate the current gain, input impedance and voltage gain.
- 46.What is MOSFET? State its principle of operation. Explain the construction and working of n-channel depletion MOSFET.
- 47.Define three parameters of JFET and hence obtain the relocation between them.
- 48. When a reverse gate voltage of 15 V is applied to a JFET, the gate current is 10^{-3} mA. Find the resistance between gate and source.
- 49.Draw the circuit diagram of a common source amplifier using a n-channel JFET. Explain its working.
- 50. Explain drain characteristics of a JFET. Define pinch off voltage.
- 51.Calculate the transconductance of JFET with change in drain current $0.3 \times 10-3$ A and change in gate to source voltage 0.3 V, when drain to source voltage is constant. Also find amplification factor if drain resistance is 33.3 kW.
- 52.Explain the transfer and output charactristics of n-Channel enhancement MOSFET with diagrams.
- 53.Show that the energy levels of a vibrating diatomic molecule are equidistant. State the selection rule.
- 54. Explain various types of molecules based on the principal moments of inertia.
- 55.Find the rotational constant of H2 molecule if H H bond is 7.4×10^{-12} meter. Given :mH = 1.67×10^{-27} kg, h = 6.626×10^{-34} J-s.
- 56.Mention the three types of quantization of molecular energies. According to it explain in short three types of molecular spectra.
- 57.State and explain selection rules for rotation-vibrational spectra of a molecule. Draw the energy level diagram for rotational vibrational spectra and show P, Q & R branches on it.
- 58. The spacing between series of lines in the microwave spectrum of Al H is constant at 12.604 cm–1 . Reduced mass of AlH molecules is 0.9718 u. Calculate the inter



Approved by government of Maharashtra

> Affiliated to Rashtrasant Tukadoji Maharaj Nagpur University, Nagpur

 Recognised by U.G.C New Delhi under section 2 (f) & 12 (b) of UGC act 1956

nuclear distance in the molecules. (h = $6.63 \times 10-17$ erg-sec 1 u = $1.67 \times 10-24$ gm).

59.Explain the intensity distribution of rotational spectral lines.